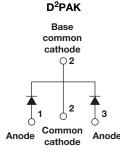
Vishay Semiconductors

FREE

# HEXFRED<sup>®</sup>, **Ultrafast Soft Recovery Diode, 8 A**



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PRODUCT SUMMARY								
Package	TO-263AB (D <sup>2</sup> PAK)							
I <sub>F(AV)</sub>	8 A							
V <sub>R</sub>	1200 V							
V <sub>F</sub> at I <sub>F</sub>	3.3 V							
t <sub>rr</sub> (typ.)	28 ns							
T <sub>J</sub> max.	150 °C							
Diode variation	Single die							

#### **FEATURES**

- Ultrafast and ultrasoft recovery
- Very low I<sub>RRM</sub> and Q<sub>rr</sub>
- Specified at operating conditions
- Meets MSL level 1, per J-STD-020, LF maximum RoHS peak of 260 °C COMPLIANT HALOGEN
- AEC-Q101 gualified
- Material categorization: For definitions of compliance please see www.vishay.com/doc?99912

#### BENEFITS

- Reduced RFI and EMI
- · Reduced power loss in diode and switching transistor
- Higher frequency operation
- Reduced snubbing
- · Reduced parts count

#### DESCRIPTION

VS-HFA08TB120S is a state of the art ultrafast recovery diode. Employing the latest in epitaxial construction and advanced processing techniques it features a superb combination of characteristics which result in performance which is unsurpassed by any rectifier previously available. With basic ratings of 1200 V and 8 A continuous current, the VS-HFA08TB120S is especially well suited for use as the companion diode for IGBTs and MOSFETs. In addition to ultrafast recovery time, the HEXFRED® product line features extremely low values of peak recovery current (I<sub>BBM</sub>) and does not exhibit any tendency to "snap-off" during the th portion of recovery. The HEXFRED features combine to offer designers a rectifier with lower noise and significantly lower switching losses in both the diode and the switching transistor. These HEXFRED advantages can help to significantly reduce snubbing, component count and heatsink sizes. The HEXFRED VS-HFA08TB120S is ideally suited for applications in power supplies and power conversion systems (such as inverters), motor drives, and many other similar applications where high speed, high efficiency is needed.

ABSOLUTE MAXIMUM RATINGS									
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS					
Cathode to anode voltage	V <sub>R</sub>		1200	V					
Maximum continuous forward current	I <sub>F</sub>	T <sub>C</sub> = 100 °C	8						
Single pulse forward current	I <sub>FSM</sub>		130	А					
Maximum repetitive forward current	I <sub>FRM</sub>		32						
Maximum power dissinction	р	T <sub>C</sub> = 25 °C	73.5	W					
Maximum power dissipation	P <sub>D</sub>	T <sub>C</sub> = 100 °C	29	vv					
Operating junction and storage temperature range	T <sub>J</sub> , T <sub>Stg</sub>		- 55 to + 150	°C					

Revision: 27-Aug-12

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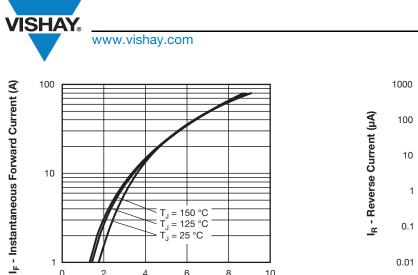
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<b>ELECTRICAL SPECIFICATIONS</b> ( $T_J = 25 \text{ °C}$ unless otherwise specified)									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Cathode to anode breakdown voltage	V <sub>BR</sub>	I <sub>R</sub> = 100 μA	1200	-	-				
Maximum forward voltage	V <sub>FM</sub>	I <sub>F</sub> = 8.0 A	-	2.6	3.3	V			
		I <sub>F</sub> = 16 A	-	3.4	4.3				
		I <sub>F</sub> = 8.0 A, T <sub>J</sub> = 125 °C	-	2.4	3.1				
Maximum reverse		V <sub>R</sub> = V <sub>R</sub> rated	-	0.31	10				
leakage current		$T_J$ = 125 °C, $V_R$ = 0.8 x $V_R$ rated	-	135	1000	μA			
Junction capacitance	CT	V <sub>R</sub> = 200 V	-	11	20	pF			
Series inductance	L <sub>S</sub>	Measured lead to lead 5 mm from package body	-	8.0	-	nH			

<b>DYNAMIC RECOVERY CHARACTERISTICS</b> ( $T_J = 25$ °C unless otherwise specified)									
PARAMETER	SYMBOL	TEST CO	NDITIONS	MIN.	TYP.	MAX.	UNITS		
Reverse recovery time	t <sub>rr</sub>	$I_F = 1.0 \text{ A}, \text{ d}I_F/\text{d}t = 200$	A/μs, V <sub>R</sub> = 30 V	-	28	-			
	t <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	63	95	ns		
	t <sub>rr2</sub>	T <sub>J</sub> = 125 °C	I <sub>F</sub> = 8.0 A dI <sub>F</sub> /dt = 200 A/μs V <sub>R</sub> = 200 V	-	106	160			
Peak recovery current	I <sub>RRM1</sub>	T <sub>J</sub> = 25 °C		-	4.5	8.0	- A nC - Α/μs		
Feak recovery current	I <sub>RRM2</sub>	T <sub>J</sub> = 125 °C		-	6.2	11			
Reverse recovery charge	Q <sub>rr1</sub>	T <sub>J</sub> = 25 °C		-	140	380			
Reverse recovery charge	Q <sub>rr2</sub>	T <sub>J</sub> = 125 °C		-	335	880			
Peak rate of fall of	dl <sub>(rec)M</sub> /dt1	T <sub>J</sub> = 25 °C		-	133	-			
recovery current during t <sub>b</sub>	dl <sub>(rec)M</sub> /dt2	T <sub>J</sub> = 125 °C		-	85	-			

THERMAL - MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS			
Lead temperature	T <sub>lead</sub>	0.063" from case (1.6 mm) for 10 s	-	-	300	°C			
Thermal resistance, junction to case	R <sub>thJC</sub>		-	-	1.7	K/W			
Thermal resistance, junction to ambient	R <sub>thJA</sub>	Typical socket mount	-	-	40	rv vv			
Weight			-	2.0	-	g			
weight			-	0.07	-	oz.			
Marking device		Case style D <sup>2</sup> PAK		HFA08	TB120S				

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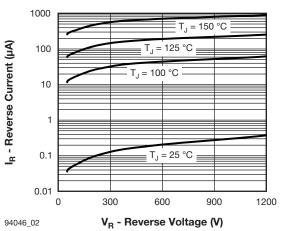


#### 10 T<sub>J</sub> = 150 °C <sup>≂</sup> T<sub>.1</sub> = 125 °C = 25 °C 8 0 2 4 6 10 V<sub>FM</sub> - Forward Voltage Drop (V) 94046\_01

Fig. 1 - Maximum Forward Voltage Drop Characteristics

## VS-HFA08TB120SPbF

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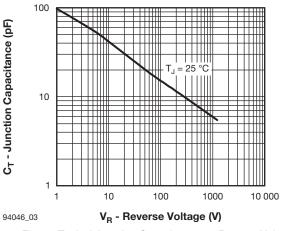


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage

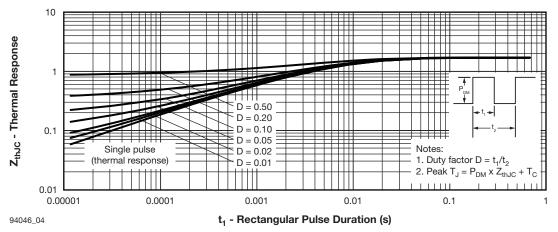


Fig. 4 - Maximum Thermal Impedance ZthJC Characteristics

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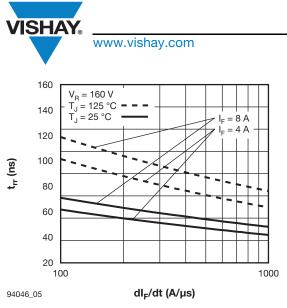


Fig. 5 - Typical Reverse Recovery Time vs. dl<sub>F</sub>/dt

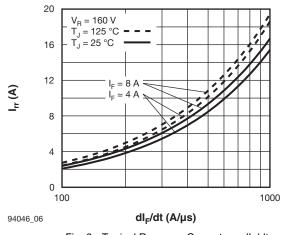
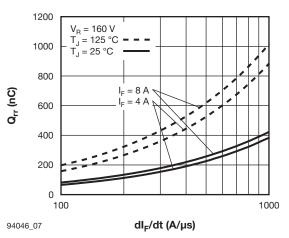


Fig. 6 - Typical Recovery Current vs. dl<sub>F</sub>/dt

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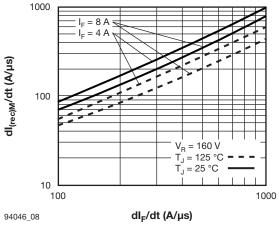


Fig. 8 - Typical dI<sub>(rec)M</sub>/dt vs. dI<sub>F</sub>/dt

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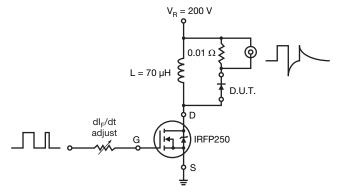
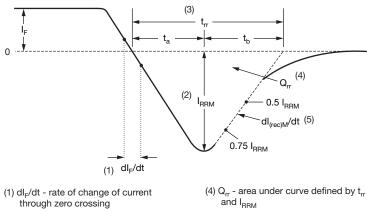
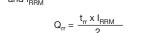


Fig. 9 - Reverse Recovery Parameter Test Circuit



(2) I<sub>RRM</sub> - peak reverse recovery current

(3)  $t_{rr}$  - reverse recovery time measured from zero crossing point of negative going I<sub>F</sub> to point where a line passing through 0.75  $I_{\rm RRM}$  and 0.50  $I_{\rm RRM}$  extrapolated to zero current.



(5) dI<sub>(re</sub> current during t<sub>b</sub> portion of t<sub>m</sub>

Fig. 10 - Reverse Recovery Waveform and Definitions

### Vishay Semiconductors

### ORDERING INFORMATION TABLE

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Т

Device code	VS-	HF	Α	08	тв	120	S	TRL	PbF
	1	2	3	4	5	6	7	8	9
	1 -	Visl	nay Sen	nicondua	ctors pro	oduct			
	2 -	HE	xFRED <sup>@</sup>	® family					
	3 -	Pro	cess de	signator	: A = El	ectron i	rradiate	d	
	4 -	Cur	rent rati	ng (08 =	= 8 A)				
	5 -	Pac	kage ou	utline (Tl	B = TO-	220, 2 I	eads)		
	6 -	Vol	tage rati	ng (120	= 1200	V)			
	7 -	- S =	D <sup>2</sup> PAK						
	8 -	• N	one = T	ube					
		• TI	RL = Ta	pe and r	eel (left	oriente	d)		
		• TI	R = Ta	pe and	reel (rig	ht orien	ted)		
	9 -	• Pł	oF = Lea	ad (Pb)-i	free				
		• P	= Lead	(Pb)-fre	e (for D	<sup>2</sup> PAK T	RR and	TRL)	

LINKS TO RELATED DOCUMENTS							
Dimensions www.vishay.com/doc?95046							
Part marking information	www.vishay.com/doc?95054						
Packaging information	www.vishay.com/doc?95032						

ORDERING INFORMATION (Example)										
PREFERRED P/N	QUANTITY PER TUBE	MINIMUM ORDER QUANTITY	PACKAGING DESCRIPTION							
VS-HFA08TB120SPBF	50	1000	Antistatic plastic tube							
VS-HFA08TB120STRRP	800	800	13" diameter reel							
VS-HFA08TB120STRLP	800	800	13" diameter reel							



## **Outline Dimensions**

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D<sup>2</sup>PAK



Conforms to JEDEC outline D<sup>2</sup>PAK (SMD-220) в Pad layout (2)(3)A 11.00 MIN.-(E) F (0.43)ŧ (3) L1 4 ( |(0.38)<sup>MIN.</sup> (D1) (3) Detail A D 17.90 (0.70) Н 15.00 (0.625) (2) З 0.15)<sup>0.01</sup> Ľ L2 Ĥ ţ В В 2.32 MIN. (0.08) 2.64 (0.103) 2.41 (0.096) (3)Г 2 x b2 С View A - A 2 x h // ± 0.004 M B ⊕ 0.010 M A M B Base Plating (4) Metal 2 x e Н b1, b3 Gauge plane c1 (4) (c) В 0° to 8° ŧ. Seating Lead assignments plane L3 A1 Lead tip (b, b2) Diodes Section B - B and C - C 1. - Anode (two die)/open (one die) Scale: None 2., 4. - Cathode Detail "A" 3. - Anode

Rotated 90 °CW Scale: 8:1

SYMBOL	MILLIMETERS		INCHES		NOTES		NOTES		NOTES		SYMBOL	MILLIN	IETERS	INC	HES	NOTES
STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES		STMBOL	MIN.	MAX.	MIN.	MAX.	NOTES				
А	4.06	4.83	0.160	0.190			D1	6.86	8.00	0.270	0.315	3				
A1	0.00	0.254	0.000	0.010			E	9.65	10.67	0.380	0.420	2, 3				
b	0.51	0.99	0.020	0.039			E1	7.90	8.80	0.311	0.346	3				
b1	0.51	0.89	0.020	0.035	4		е	2.54	BSC	0.100	BSC					
b2	1.14	1.78	0.045	0.070			Н	14.61	15.88	0.575	0.625					
b3	1.14	1.73	0.045	0.068	4		L	1.78	2.79	0.070	0.110					
с	0.38	0.74	0.015	0.029			L1	-	1.65	-	0.066	3				
c1	0.38	0.58	0.015	0.023	4		L2	1.27	1.78	0.050	0.070					
c2	1.14	1.65	0.045	0.065			L3 0.25 BSC 0.010 BSC		BSC							
D	8.51	9.65	0.335	0.380	2		L4	4.78	5.28	0.188	0.208					

#### Notes

 $^{(1)}\,$  Dimensioning and tolerancing per ASME Y14.5 M-1994  $\,$ 

(2) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outmost extremes of the plastic body

<sup>(3)</sup> Thermal pad contour optional within dimension E, L1, D1 and E1

<sup>(4)</sup> Dimension b1 and c1 apply to base metal only

<sup>(5)</sup> Datum A and B to be determined at datum plane H

<sup>(6)</sup> Controlling dimension: inch

<sup>(7)</sup> Outline conforms to JEDEC outline TO-263AB

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#### **DIMENSIONS** in millimeters and inches



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